

Supplementary information

Highly doped silicon nanowires by monolayer doping

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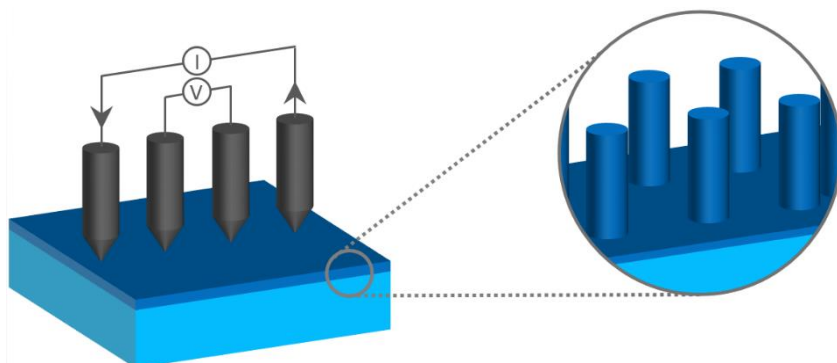


Figure S1. Schematic of the four-point probe set-up to measure the resistivity of the nanowire samples.

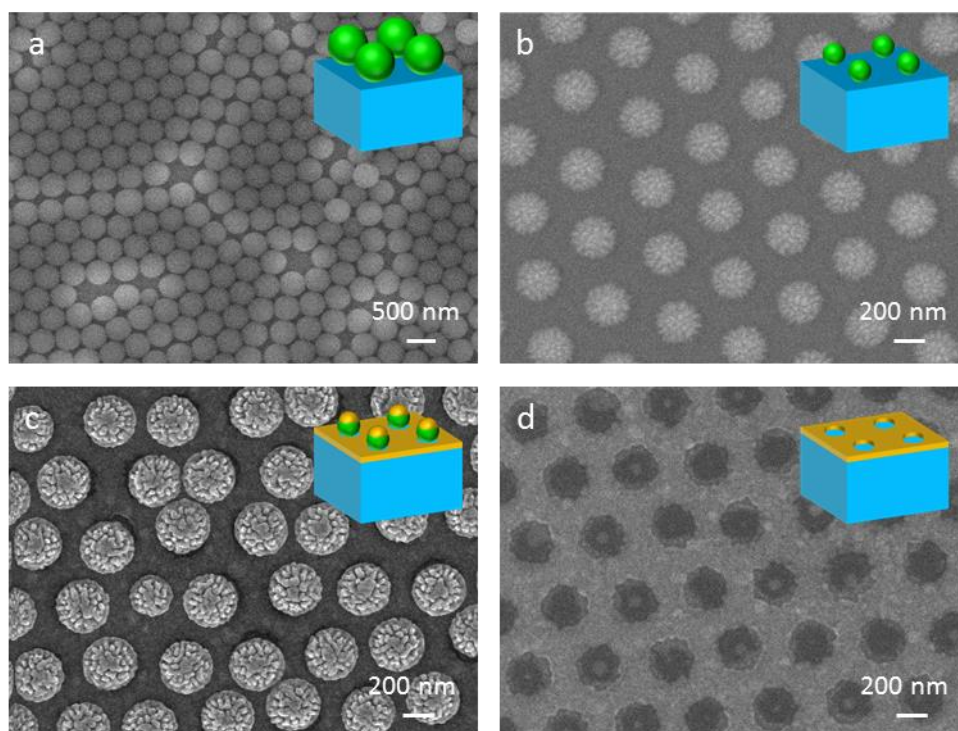


Figure S2. Top-view HR-SEM images of samples resulting from nanosphere lithography, including a) close-packed array formation of polystyrene spheres, b) diameter decrease by oxygen reactive-ion etching, c) silver sputtering on top, d) lift-off of polystyrene spheres.